

OptiMOS2 Power-Transistor

Manufacturers	Infineon Technologies Corporation
Package/Case	TDSON-8
Product Type	Transistors
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for BSC022N03S or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

BSC022N03S is a power MOSFET (metal-oxide-semiconductor field-effect transistor) designed and manufactured by Infineon Technologies. It is a N-channel MOSFET with a maximum drain-source voltage rating of 30V and a maximum continuous drain current rating of 220A.

Features

Low on-resistance (0.0022 ohms at 10V gate-source voltage)

Fast switching speed (13ns rise time, 27ns fall time)

Low gate charge (120nC)

Avalanche-rated

Application

Switching power supplies

Motor control

DC-DC converters

Battery protection circuits

Audio amplifiers



Related Products



[BSP613P](#)

Infineon Technologies Corporation
SOT-223



[BSC011N03LS](#)

Infineon Technologies Corporation
PG-TDSON-8



[BSB013NE2LXI](#)

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[BSC014N04LSATMA1](#)

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[BSC030N08NS5ATMA1](#)

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TDSON-8